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November 2013

# FQP3P20

# P-Channel QFET® MOSFET

-200 V, -2.8 A, 2.7 Ω

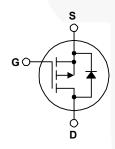
# **Description**

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance • Low Crss (Typ 7.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

### **Features**

- -2.8 A, -200 V,  $R_{DS(on)}$  = 2.7  $\Omega$  (Max.) @  $V_{GS}$  = -10 V,  $I_D = -1.4 A$
- Low Gate Charge (Typ. 6 nC)





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP3P20	Unit
$V_{DSS}$	Drain-Source Voltage		-200	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		-2.8	Α
	- Continuous (T <sub>C</sub> = 100°C)		-1.77	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-11.2	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	150	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	-2.8	Α
E <sub>AR</sub>	Repetitive Avalanche Energy		5.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		-5.5	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		52	W
	- Derate above 25°C		0.42	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

# **Thermal Characteristics**

Symbol	Parameter	FQP3P20	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.4	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP3P20	FQP3P20	TO-220	Tube	N/A	N/A	50 units

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-200			V
ΔBV <sub>DSS</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = -250 μA, Referenced to 25°C		-0.18		V/°C
I <sub>DSS</sub>		V <sub>DS</sub> = -200 V, V <sub>GS</sub> = 0 V			-1	μΑ
Zero Gate Voltage Dra	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -160 V, T <sub>C</sub> = 125°C			-10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-3.0		-5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -1.4 A		2.06	2.7	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -40 V, I <sub>D</sub> = -1.4 A		1.23		S
	ic Characteristics			ı	ı	
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		190	250	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		45	60	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			7.5	10	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V - 400 V I - 0.0 A		8.5	25	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = -100 \text{ V}, I_{D} = -2.8 \text{ A},$ $R_{G} = 25 \Omega$		35	80	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	11.6 20 32		12	35	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		25	60	ns
Qg	Total Gate Charge	V <sub>DS</sub> = -160 V, I <sub>D</sub> = -2.8 A,		6.0	8.0	nC
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = -10 V		1.7		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	/	2.9		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-2.8	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				-11.2	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -2.8 A			-5.0	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -2.8 A,		100		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> / dt = 100 A/μs		0.34	//	μC

- 1. Repetitive rating : pulse-width limited by maximum junction temperature.
- 2. L = 29 mH, I<sub>AS</sub> = 2.8 A, V<sub>DD</sub> = -50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  -2.8 A, di/dt  $\leq$  300 A/µs , V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature.

# **Typical Characteristics**

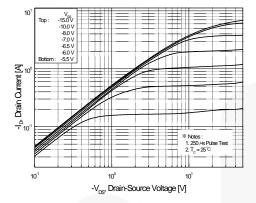


Figure 1. On-Region Characteristics

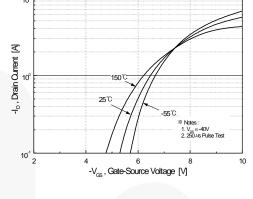


Figure 2. Transfer Characteristics

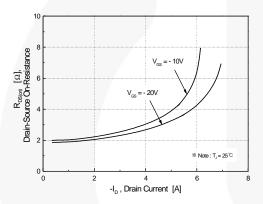


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

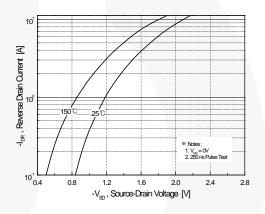


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

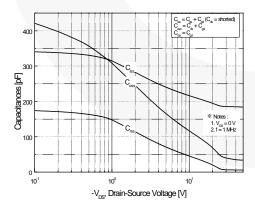


Figure 5. Capacitance Characteristics

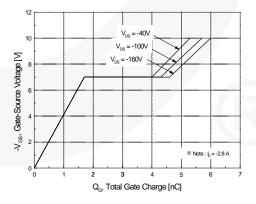


Figure 6. Gate Charge Characteristics

# Typical Characteristics (Continued)

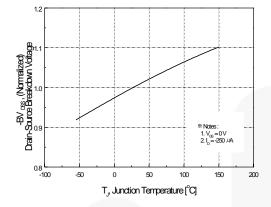


Figure 7. Breakdown Voltage Variation vs. Temperature

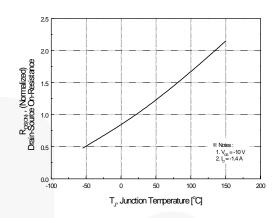


Figure 8. On-Resistance Variation vs. Temperature

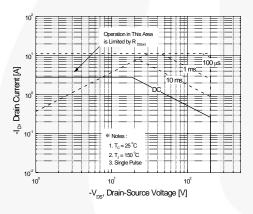


Figure 9. Maximum Safe Operating Area

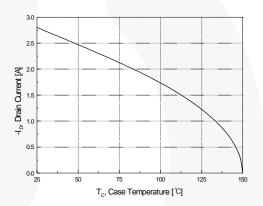


Figure 10. Maximum Drain Current vs. Case Temperature

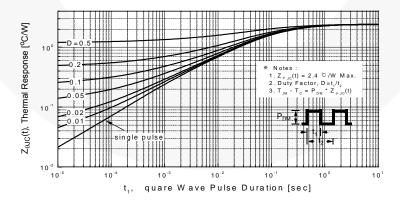


Figure 11. Transient Thermal Response Curve

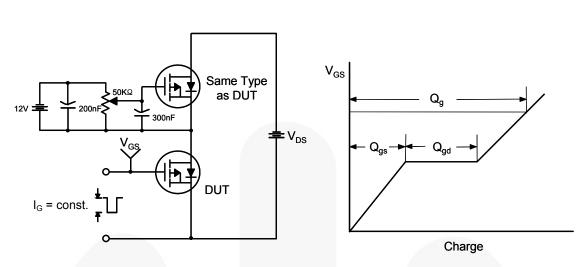


Figure 12. Gate Charge Test Circuit & Waveform

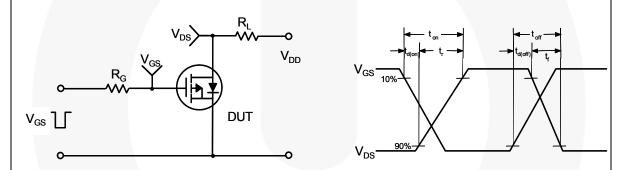


Figure 13. Resistive Switching Test Circuit & Waveforms

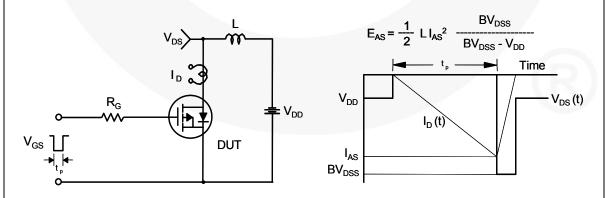
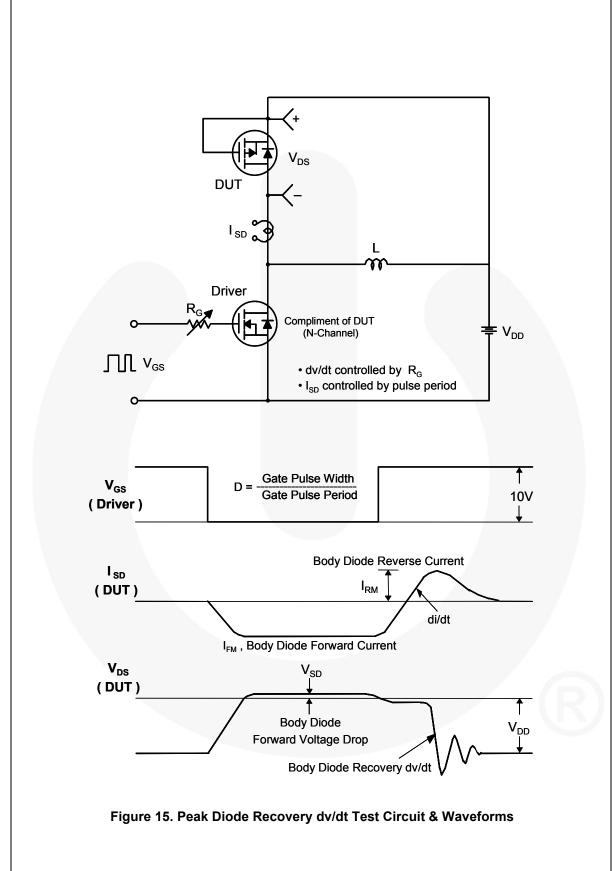


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



# **Mechanical Dimensions**

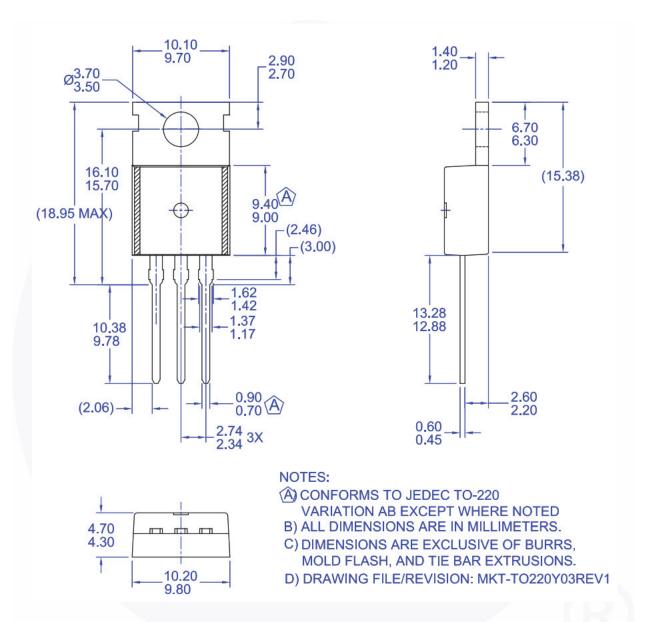


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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